TOSHIBA Field Effect Transistor Silicon N Channel MOS Type ( $\pi$ -MOSVII)

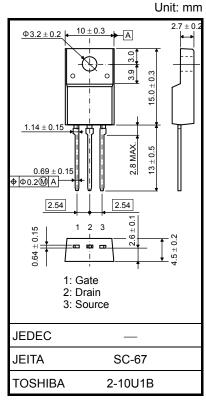
# TK15A60D

#### Switching Regulator Applications

- Low drain-source ON-resistance: RDS (ON) =  $0.31 \Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 8.5 \text{ S} (typ.)$
- Low leakage current:  $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 600 \ V)$
- Enhancement mode:  $V_{th}$  = 2.0 to 4.0 V ( $V_{DS}$  = 10 V,  $I_D$  = 1 mA)

| <b>.</b> ,                                    |           |        |                  |            |      |  |  |  |
|---|-----------|--------|------------------|------------|------|--|--|--|
| Characteristics                               |           |        | Symbol           | Rating     | Unit |  |  |  |
| Drain-source voltage                          |           |        | V <sub>DSS</sub> | 600        | V    |  |  |  |
| Gate-source voltage                           |           |        | V <sub>GSS</sub> | ±30        | V    |  |  |  |
| Drain current                                 | DC (No    | ote 1) | ۱ <sub>D</sub>   | 15         | А    |  |  |  |
|   | Pulse (No | ote 1) | I <sub>DP</sub>  | 60         | A    |  |  |  |
| Drain power dissipation (Tc = $25^{\circ}$ C) |           |        | PD               | 50         | W    |  |  |  |
| Single pulse avalanche energy<br>(Note 2)     |           |        | E <sub>AS</sub>  | 527        | mJ   |  |  |  |
| Avalanche current                             |           |        | I <sub>AR</sub>  | 15         | А    |  |  |  |
| Repetitive avalanche energy (Note 3)          |           |        | E <sub>AR</sub>  | 5.0        | mJ   |  |  |  |
| Channel temperature                           |           |        | T <sub>ch</sub>  | 150        | °C   |  |  |  |
| Storage temperature range                     |           |        | T <sub>stg</sub> | -55 to 150 | °C   |  |  |  |

#### Absolute Maximum Ratings (Ta = 25°C)



Weight: 1.7 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

#### Thermal Characteristics

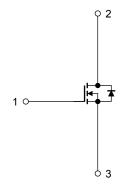
| Characteristics                        | Symbol                 | Max  | Unit |  |
|--|------------------------|------|------|--|
| Thermal resistance, channel to case    | R <sub>th (ch-c)</sub> | 2.5  | °C/W |  |
| Thermal resistance, channel to ambient | R <sub>th (ch-a)</sub> | 62.5 | °C/W |  |

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2:  $V_{DD} = 90 \text{ V}, \text{ T}_{ch} = 25^{\circ}C(\text{initial}), \text{ L} = 4.1 \text{ mH}, \text{ R}_{G} = 25 \Omega, \text{ I}_{AR} = 15 \text{ A}$ 

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Handle with care.



Start of commercial production 2009-01

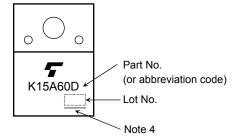
Electrical Characteristics (Ta = 25°C)

| Char                         | acteristics   | Symbol               | Test Condition  | Min | Тур. | Max  | Unit |
|------------------------------|---|----------------------|---|-----|------|------|------|
| Gate leakage current         |   | I <sub>GSS</sub>     | $V_{GS}=\pm 30~V,~V_{DS}=0~V$   | _   | _    | ±1   | μA   |
| Drain cut-off current        |   | I <sub>DSS</sub>     | $V_{DS} = 600 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$  |     | _    | 10   | μA   |
| Drain-source bre             | Drain-source breakdown voltage                                |                      | $I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$   | 600 | _    | _    | V    |
| Gate threshold v             | oltage  | V <sub>th</sub>      | $V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$   | 2.0 | _    | 4.0  | V    |
| Drain-source ON              | resistance  | R <sub>DS (ON)</sub> | $V_{GS} = 10 \text{ V}, \text{ I}_{D} = 7.5 \text{ A}$  |     | 0.31 | 0.37 | Ω    |
| Forward transfer             | ransfer admittance $ Y_{fs} $ $V_{DS} = 10 V$ , $I_D = 7.5 A$ |                      | $V_{DS} = 10 \text{ V}, \text{ I}_{D} = 7.5 \text{ A}$  | 2.4 | 8.5  | _    | S    |
| Input capacitance            |   | C <sub>iss</sub>     |   |     | 2600 |      |      |
| Reverse transfer capacitance |   | C <sub>rss</sub>     | V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1 MHz  | _   | 11   | _    | pF   |
| Output capacitance           |   | C <sub>oss</sub>     |   |     | 280  |      |      |
| Switching time               | Rise time   | tr                   | $V_{GS}$ $0 V$ $V_{GS}$ $0 V$ | _   | 50   |      | - ns |
|                              | Turn-on time  | t <sub>on</sub>      |   |     | 100  |      |      |
|                              | Fall time   | t <sub>f</sub>       |   | _   | 25   | _    |      |
|                              | Turn-off time   | t <sub>off</sub>     | Duty $\leq$ 1%, t <sub>W</sub> = 10 µs  |     | 150  | _    |      |
| Total gate charge            |   | Qg                   |   |     | 45   |      |      |
| Gate-source charge           |   | Q <sub>gs</sub>      | V <sub>DD</sub> ≈ 400 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 15 A  |     | 28   |      | nC   |
| Gate-drain charge            |   | Q <sub>gd</sub>      | ]   |     | 17   |      |      |

#### Source-Drain Ratings and Characteristics (Ta = 25°C)

| Characteristics                           | Symbol           | Test Condition                                 | Min | Тур. | Max  | Unit |
|---|------------------|--|-----|------|------|------|
| Continuous drain reverse current (Note 1) | I <sub>DR</sub>  | —  | _   | _    | 15   | А    |
| Pulse drain reverse current (Note 1)      | I <sub>DRP</sub> | —  | _   | _    | 60   | А    |
| Forward voltage (diode)                   | V <sub>DSF</sub> | I <sub>DR</sub> = 15 A, V <sub>GS</sub> = 0 V  | _   | _    | -1.7 | V    |
| Reverse recovery time                     | t <sub>rr</sub>  | I <sub>DR</sub> = 15 A, V <sub>GS</sub> = 0 V, | _   | 1700 | _    | ns   |
| Reverse recovery charge                   | Qrr              | dl <sub>DR</sub> /dt = 100 A/μs                | _   | 26   | _    | μC   |

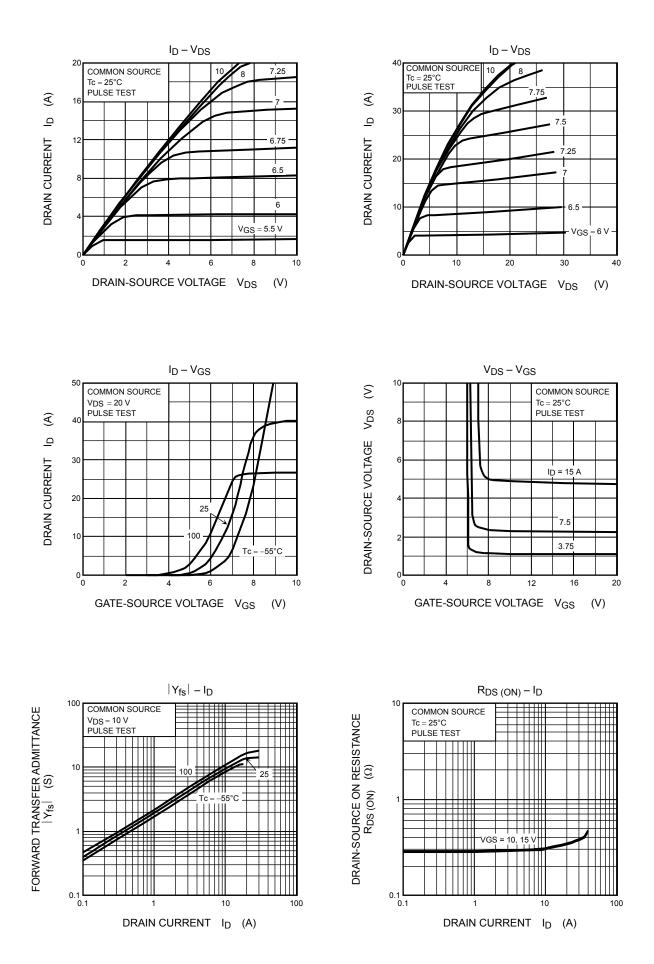
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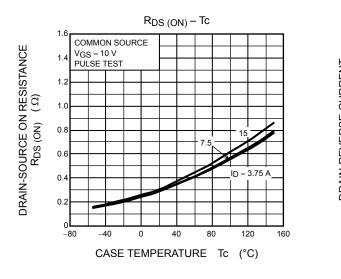
Note 4 : A line under a Lot No. identifies the indication of product Labels [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

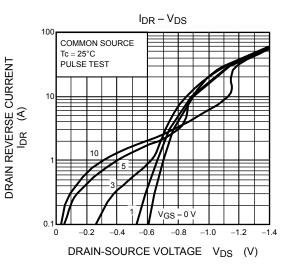
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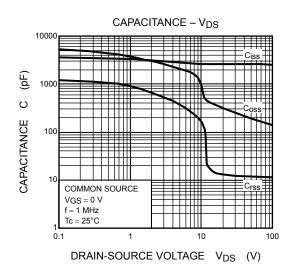
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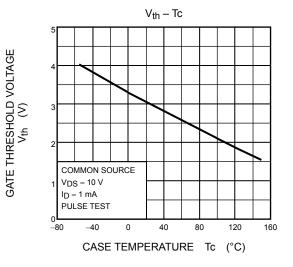


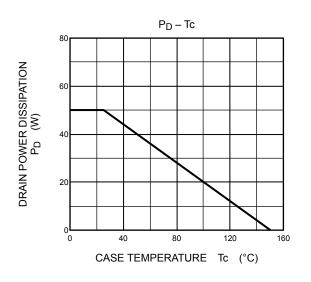
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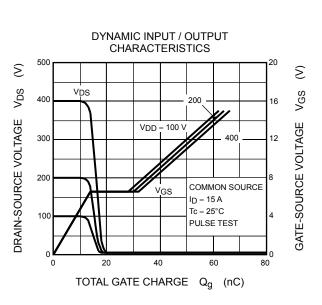


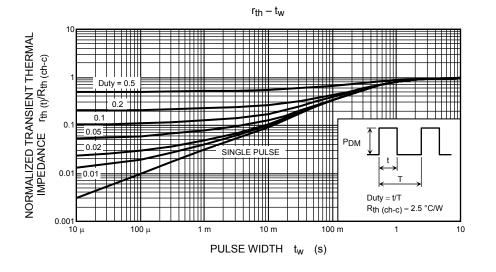




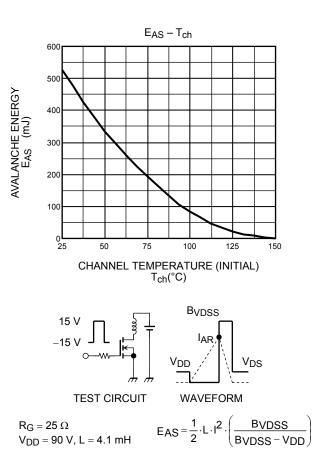








SAFE OPERATING AREA 100 ID max (pulsed) \* ŦŦŧ 100 us (continuous) 1 ms 10  $\overline{\mathsf{A}}$ DRAIN CURRENT ID DC operation Tc = 25°C 0.1 \*: SINGLE NONREPETITIVE PULSE Tc = 25°C 0.01 CURVES MUST BE DERATED LINEARLY WITH INCREASE IN TEMPERATURE VDSS max 0.001 10 100 1000 DRAIN-SOURCE VOLTAGE VDS (V)



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